

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 1.53(b) Divisional Application of USSN: 09/274,767

SHIMOYAMA, et al.

Group Art Unit: **2828 (expected)**

Serial No.: **Not Yet Assigned**

Examiner: **Quyen Phan Leung (expected)**

Filed: **Herewith**

For. **SEMICONDUCTOR LIGHT-EMITTING DEVICE**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

September 2, 2003

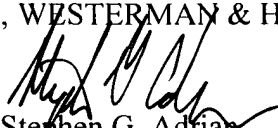
Sir:

This Information Disclosure Statement is being filed in order to comply with Applicant's duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent application Serial No. 09/274,767.

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP


Stephen G. Adrian
Attorney for Applicants
Reg. No. 32,878

SGA/rer
Atty. Docket No. **990342A**
Suite 1000
1725 K Street, N.W.
Washington, D.C. 20006
(202) 659-2930



23850

PATENT TRADEMARK OFFICE

Enclosure: PTO-1449

| | | |
|---|--|--|
| INFORMATION DISCLOSURE CITATION PTO-1449 | Atty. Docket No. 990342A | Serial No. Not Yet Assigned |
| | Applicant(s): SHIMOYAMA, et al. | |
| | Filing Date: September 2, 2003 | Group Art Unit: 2828 (expected) |

U.S. PATENT DOCUMENTS

| Examiner Initial | | Document No. | Name | Date | Class | Subclass | Filing Date (If appropriate) |
|---------------------|----|--------------|---------------|---------|-------|----------|---------------------------------|
| _____ | AA | 5,003,549 | Mitsui et al. | 3/1991 | 372 | 46 | |
| _____ | AB | 5,465,266 | Bour et al. | 11/1995 | | | |
| _____ | AC | 4,622,673 | Tsang | 11/1986 | 372 | 45 | |

FOREIGN PATENT DOCUMENTS

| | | Document No. | Date | Country | Translation (Yes or No) |
|-------|----|--------------|---------|----------|----------------------------|
| _____ | AD | EP 0 867 949 | 9/30/98 | European | |
| _____ | AE | EP 0 469 301 | 6/29/90 | European | |
| _____ | AF | | | | |

OTHER DOCUMENTS

| | | | | |
|--|-----------------|--|----------|-----------------|
| _____ | AG | LIN J-F ET AL: "High temperature and low threshold current operation of strained AlGaInP/Ga _{0.4} In _{0.6} P multiple quantum well laser diodes emitting at 676 nm" vol. 30, no. 6, pages 494-495, March 1994. | | |
| _____ | AH | Patent Abstracts of Japan; vol. 017, no. 065 (E-1317); February 9, 1993 & JP 04 269886 A (Toshiba Corp.), 9/25/92). | | |
| _____ | AI | Patent Abstracts of Japan; vol. 1997, no. 11, November 28, 1997 & JP 09 199791 A (NNEC Corp), July 31, 1997 | | |
| <table border="1" style="width: 100%;"> <tr> <td style="width: 50%;">Examiner</td> <td style="width: 50%;">Date Considered</td> </tr> </table> | | | Examiner | Date Considered |
| Examiner | Date Considered | | | |